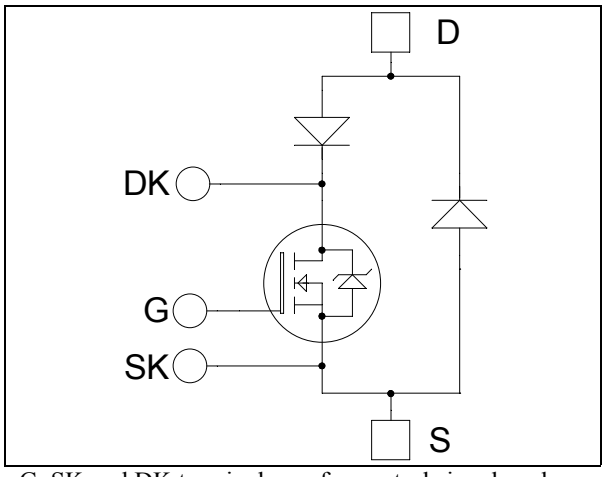
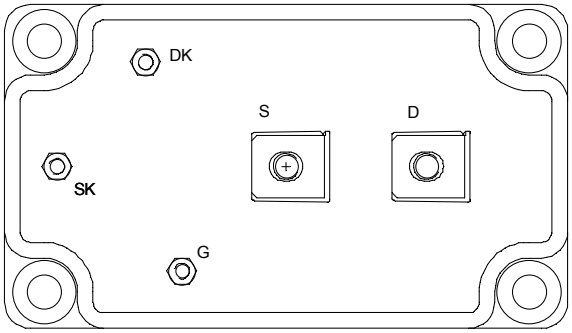
APTM100UM65SCAVG

Single switch
Series & SiC parallel diodes
MOSFET Power Module

V_{DSS} = 1000V
R_{DSon} = 65mΩ typ @ Tj = 25°C
I_D = 145A @ Tc = 25°C



G, SK and DK terminals are for control signals only (not for power)



Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- ***Power MOS 7® MOSFETs***
  - Low R_{DSon}
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- ***SiC Parallel Schottky Diode***
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature Independent switching behavior
  - Positive temperature coefficient on VF
- Kelvin source for easy drive
- Kelvin drain for voltage monitoring
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
  - M3 power connectors
- High level of integration
- AlN substrate for improved MOSFET thermal performance

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{DSS}	Drain - Source Voltage		1000	V
I_D	Continuous Drain Current	T_c = 25°C	145	A
		T_c = 80°C	110	
I_{DM}	Pulsed Drain current		580	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		78	mΩ
P_D	Power Dissipation	T_c = 25°C	3250	W
I_{AR}	Avalanche current (repetitive and non repetitive)		30	A
E_{AR}	Repetitive Avalanche Energy		50	mJ
E_{AS}	Single Pulse Avalanche Energy		3200	

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS}= 1000V	T_j = 25°C			400	µA
		V_{GS} = 0V, V_{DS}= 800V	T_j = 125°C			2	mA
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 72.5A			65	78	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 20mA		3		5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±30 V, V_{DS} = 0V				±400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		28.5		nF
C_{oss}	Output Capacitance			5.08		
C_{rss}	Reverse Transfer Capacitance			0.9		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 500V I_D = 145A		1068		nC
Q_{gs}	Gate – Source Charge			136		
Q_{gd}	Gate – Drain Charge			692		
$T_{d(on)}$	Turn-on Delay Time	V_{GS} = 15V V_{Bus} = 670V I_D = 145A R_G = 0.75Ω		18		ns
T_r	Rise Time			14		
$T_{d(off)}$	Turn-off Delay Time			140		
T_f	Fall Time			55		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 670V I_D = 145A, R_G = 0.75Ω		2.9		mJ
E_{off}	Turn-off Switching Energy			2.9		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 670V I_D = 145A, R_G = 0.75Ω		4.8		mJ
E_{off}	Turn-off Switching Energy			3.9		
R_{thJC}	Junction to Case Thermal Resistance				0.038	°C/W

Series diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					1000	V
I_{RM}	Reverse Leakage Current	V_R=1000V				500	µA
I_F	DC Forward Current		T_c = 25°C		240		A
V_F	Diode Forward Voltage	I_F = 240A			1.9	2.5	V
		I_F = 480A			2.2		
		I_F = 240A	T_j = 125°C		1.7		
t_{rr}	Reverse Recovery Time	I_F = 240A V_R = 667V di/dt = 800A/µs	T_j = 25°C		280		ns
			T_j = 125°C		350		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		3		µC
			T_j = 125°C		14.4		
R_{thJC}	Junction to Case Thermal Resistance					0.23	°C/W

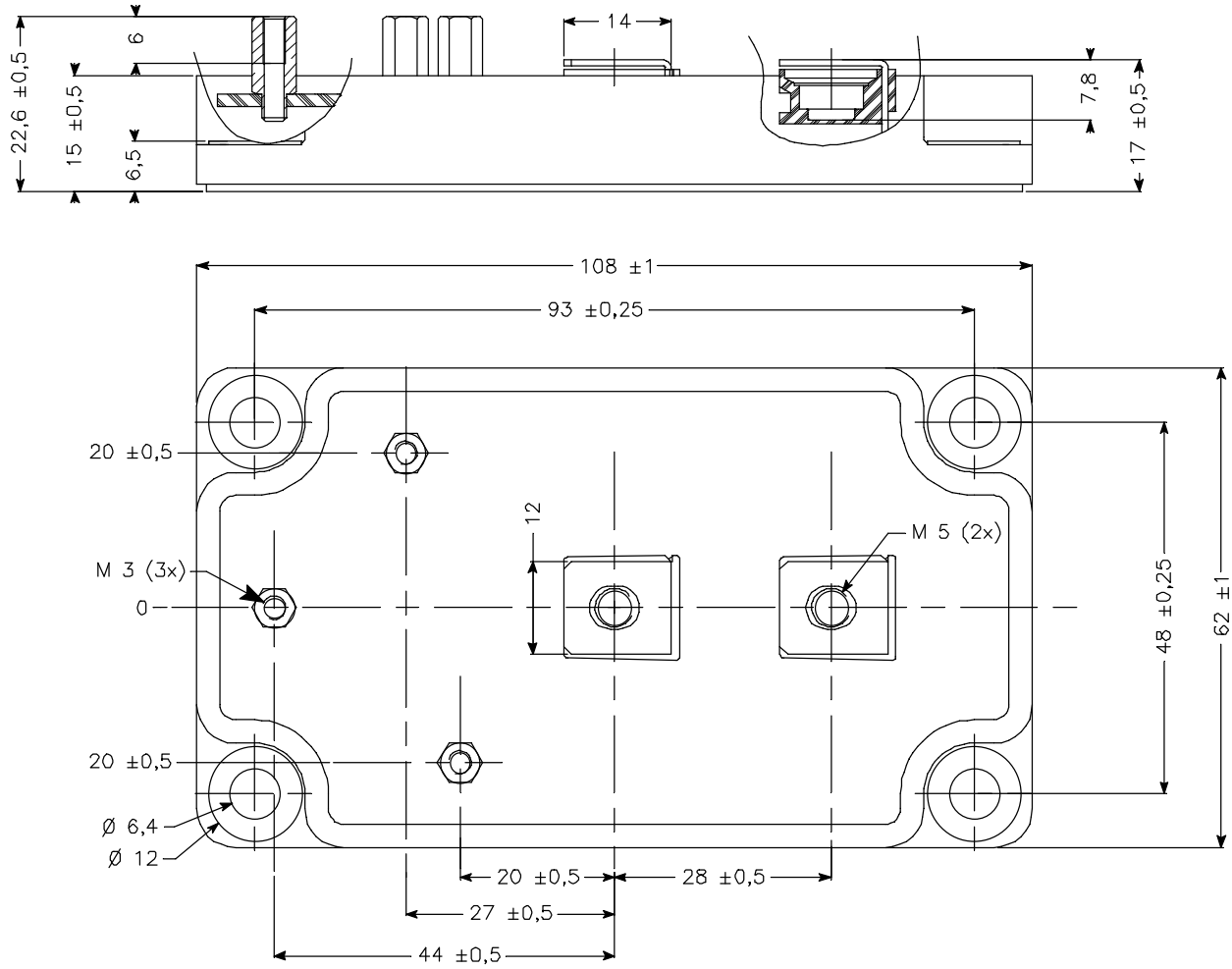
SiC Parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					1200	V
I_{RM}	Reverse Leakage Current	V_R=1200V	T_j = 25°C		384	2400	µA
			T_j = 175°C		672	12000	
I_F	DC Forward Current		Tc = 100°C		120		A
V_F	Diode Forward Voltage	I_F = 120A	T_j = 25°C		1.6	1.8	V
			T_j = 175°C		2.3	3.0	
Q_C	Total Capacitive Charge	I_F = 120A, V_R = 1200V di/dt =5000A/µs			960		nC
C	Total Capacitance	f = 1MHz, V_R = 200V			1152		pF
		f = 1MHz, V_R = 400V			828		
R_{thJC}	Junction to Case Thermal Resistance					0.18	°C/W

Thermal and package characteristics

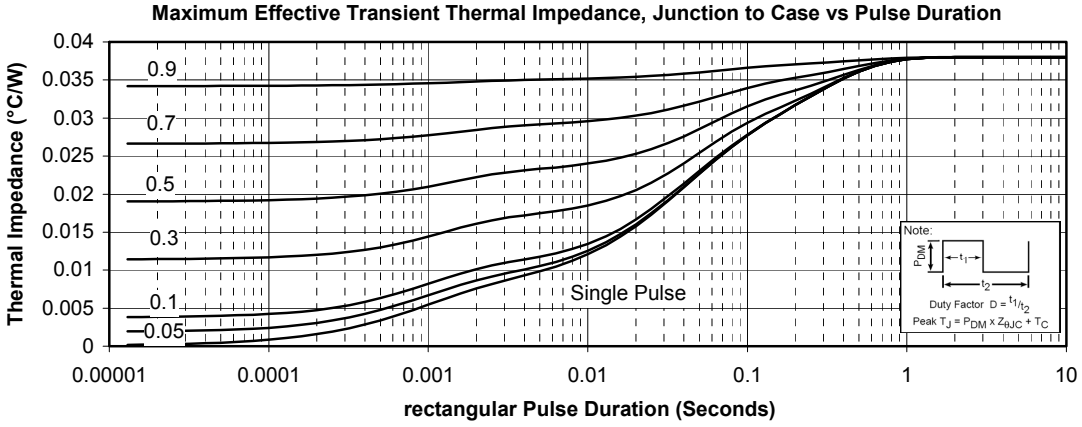
Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T_J	Operating junction temperature range			-40	150	°C
T_{JOP}	Recommended junction temperature under switching conditions			-40	$T_J$max -25	
T_{STG}	Storage Temperature Range			-40	125	
T_C	Operating Case Temperature			-40	100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
			M3	1	1.5	
Wt	Package Weight				300	g

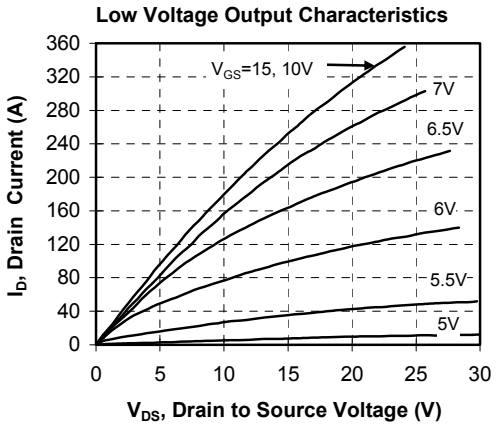
SP6 Package outline (dimensions in mm)

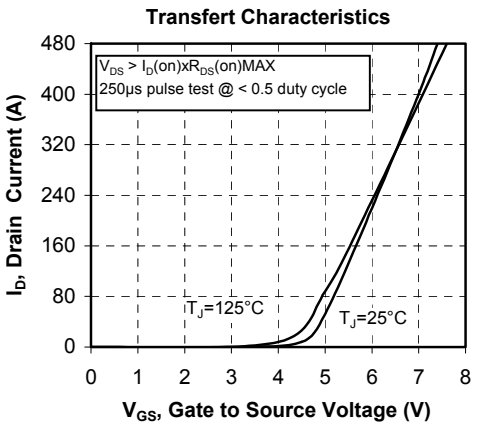


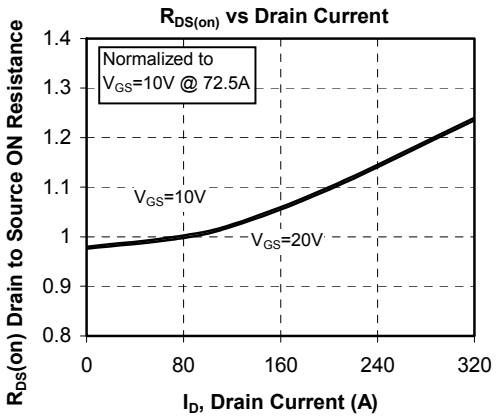
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

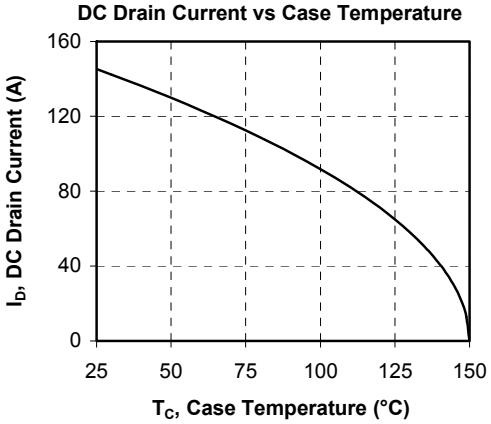
Typical MOSFET Performance Curve



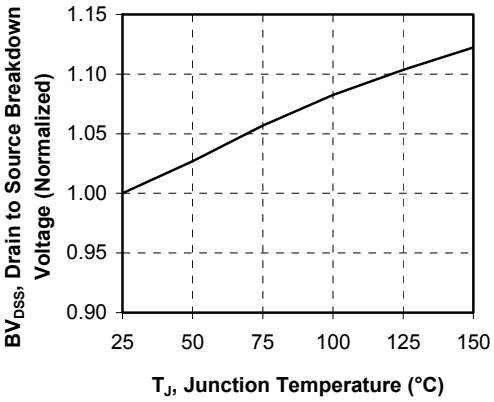




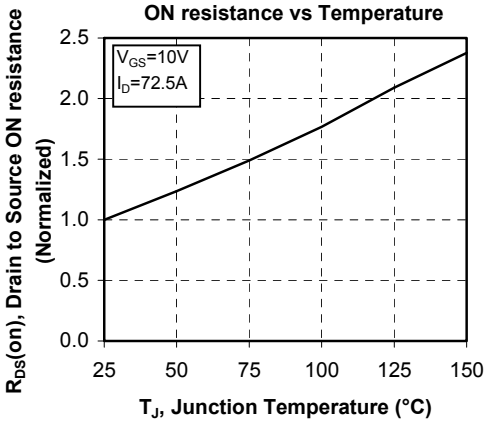




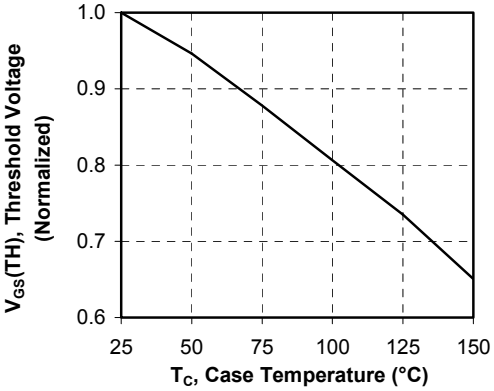
Breakdown Voltage vs Temperature



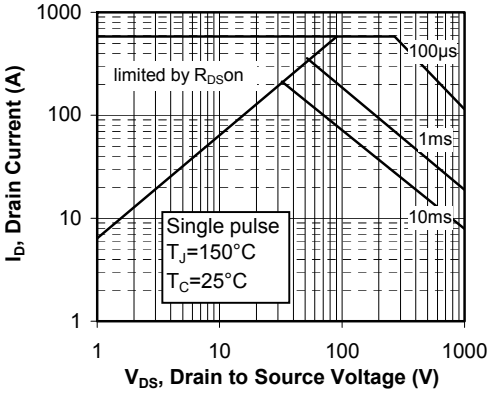
ON resistance vs Temperature



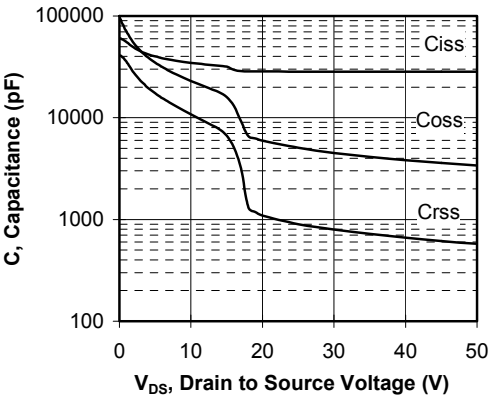
Threshold Voltage vs Temperature



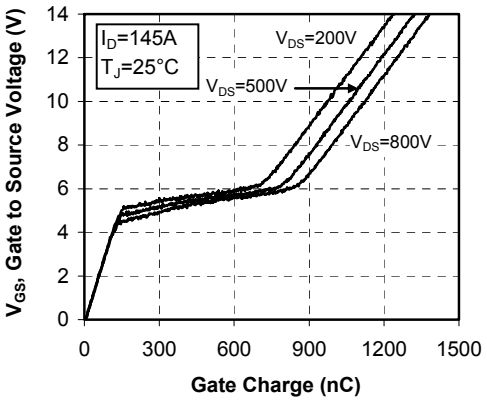
Maximum Safe Operating Area



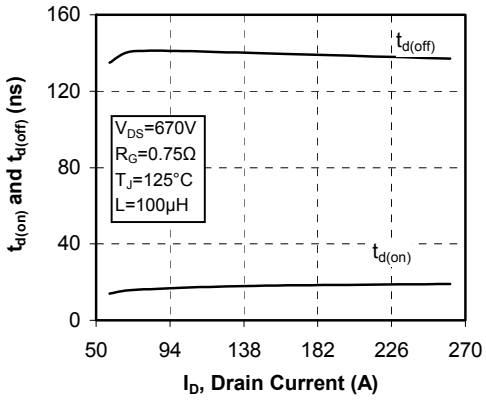
Capacitance vs Drain to Source Voltage



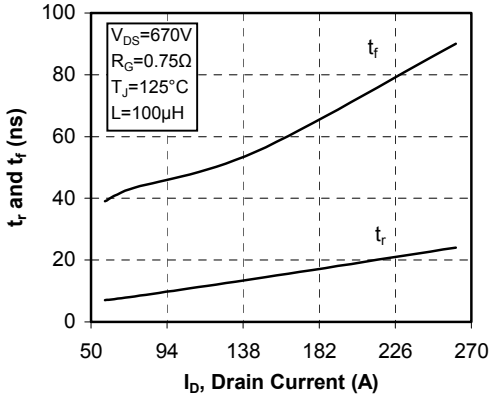
Gate Charge vs Gate to Source Voltage



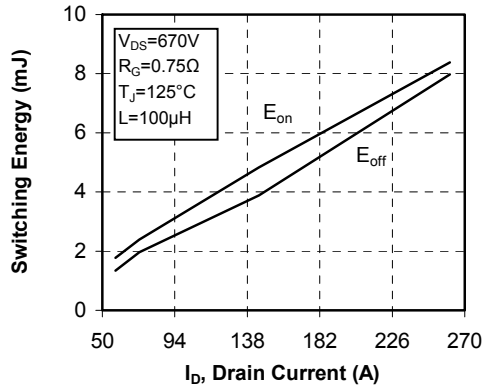
Delay Times vs Current



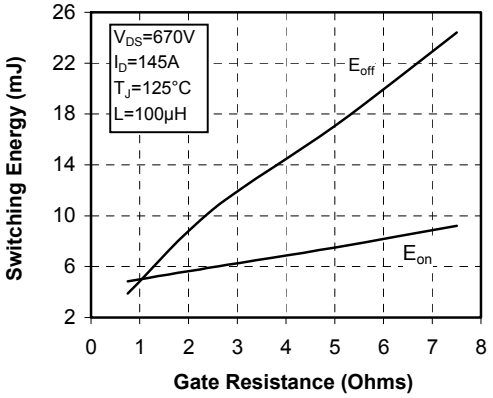
Rise and Fall times vs Current



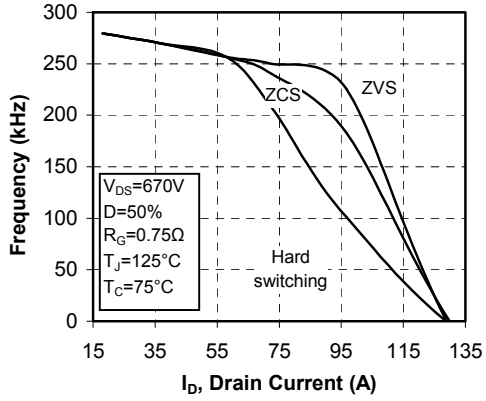
Switching Energy vs Current



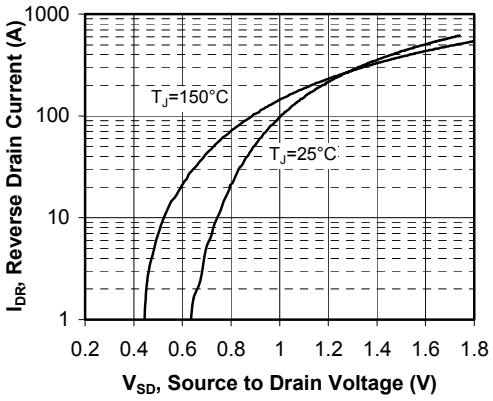
Switching Energy vs Gate Resistance



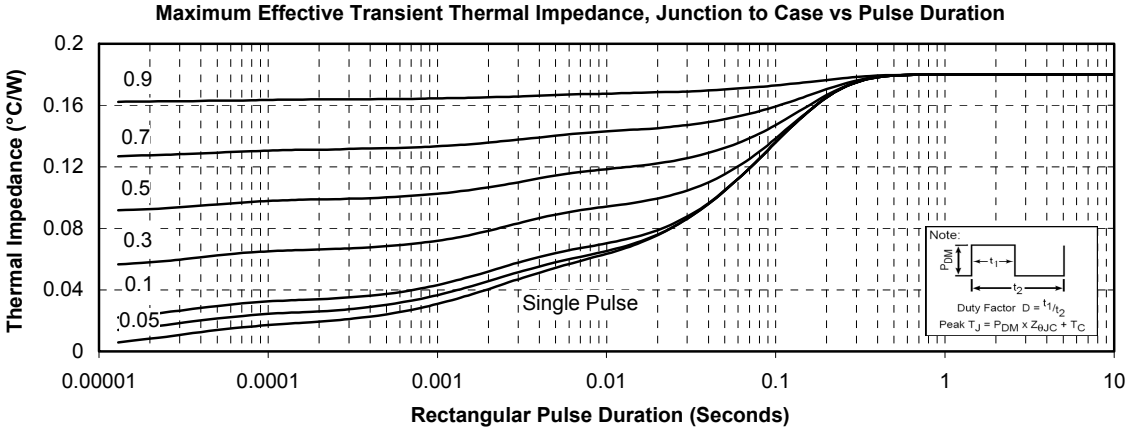
Operating Frequency vs Drain Current

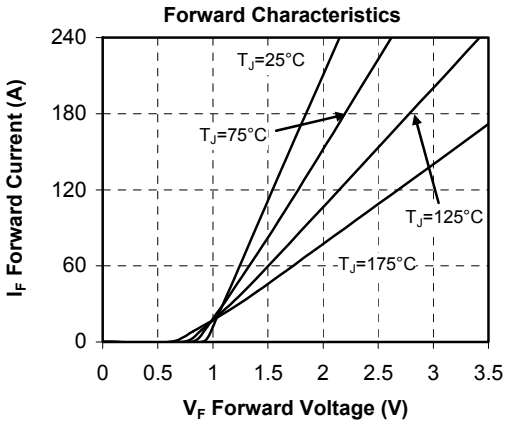


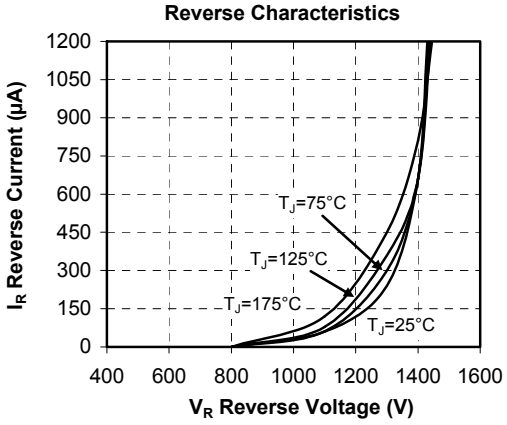
Source to Drain Diode Forward Voltage

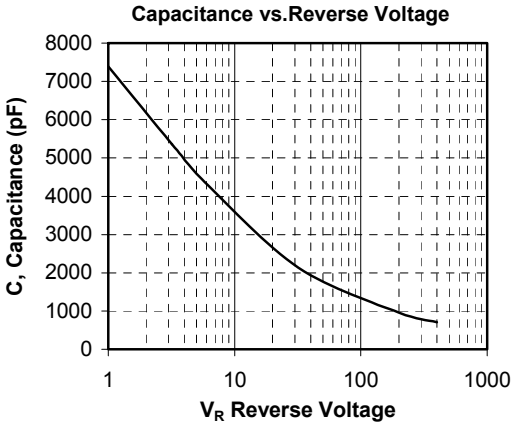


Typical SiC Diode Performance Curve









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